

NEW!
Two & Three
Section Models

MMIC

REFLECTIONLESS FILTERS DICE

50Ω DC to 21 GHz

The Big Deal

- High Stopband rejection, up to 50 dB
- Patented design terminates stopband signals
- Pass band cut-off up to 11 GHz
- Stop band up to 26 GHz
- Excellent repeatability through IPD* process



X-Series

Available in Low Pass
and High Pass designs

Product Overview

Mini-Circuits' **X-Series** of reflectionless filters now includes 2- and 3-section models, giving you ultra-high rejection in the stopband – up to 50 dB! Reflectionless filters employ a patented filter topology which absorbs and terminates stopband signals internally rather than reflecting them back to the source. This new capability enables unique applications for filter circuits beyond those suited to traditional approaches. Traditional filters are reflective in the stopband, sending signals back to the source at 100% power. These reflections interact with neighboring components and often result in intermodulation and other interferences. By eliminating stopband reflections, reflectionless filters can readily be paired with sensitive devices and used in applications that otherwise require circuits such as isolation amplifiers or attenuators.

Key Features	Advantages
Easy integration with sensitive reflective components, e.g. mixers, multipliers	Reflectionless filters absorb unwanted signals, preventing reflections back to the source. This reduces generation of additional unwanted signals without the need for extra components like attenuators, improving system dynamic range and saving board space.
High stopband rejection, up to 50 dB	Ideal for applications where suppression of strong spurious signals and intermodulation products is needed.
Enables stable integration of wideband amplifiers	Because reflectionless filters maintain good impedance in the stopband; they can be integrated with high gain, wideband amplifiers without the risk of creating instabilities in these out of band regions.
Cascadable	Reflectionless filters can be cascaded in multiple sections to provide sharper and higher attenuation, while also preventing any standing waves that could affect passband signals. Low & highpass filters can be cascaded to realize bandpass filters.
Excellent power handling in a tiny surface mount device up to 7W in passband	High power handling extends the usability of these filters to the transmit path for inter-stage filtering.
Excellent repeatability of RF performance	Through semiconductor IPD process, X-series filters are inherently repeatable for large volume production.
Excellent stability over temperature	With ± 0.3 dB variation over temperature ideal for use in wide temperature range applications without the need for additional temperature compensation.
Operating temperature up to 105°C	Suitable for operation close to high power components.

*IPD – Integrated Passive Device, is a GaAs semiconductor process



Reflectionless Low Pass Filter Die

XLF-362H-D+

50Ω DC to 3910 MHz

Features

- Match to 50Ω in the stop band, eliminates undesired reflections
- Cascadable
- Excellent stopband rejection, 48 dB typ.
- Temperature stable, up to 105°C
- Protected by US Patents 8,392,495; 9,705,467, additional patent pending
- Protected by China Patent 201080014266.1
- Protected by Taiwan Patent I581494

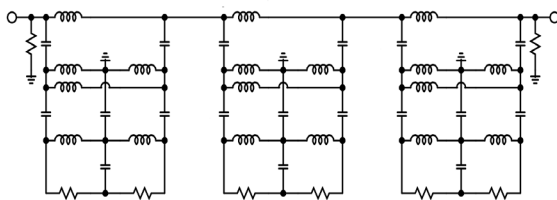
Applications

- ISM Applications
- Mobile
- WiMAX
- Radio location.

General Description

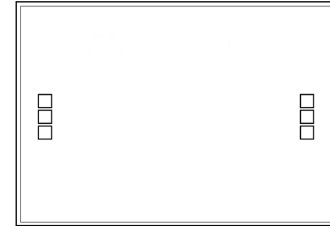
Mini-Circuits' XLF-362H-D+ three-section reflectionless filter Die employs a novel filter topology which absorbs and terminates stop band signals internally rather than reflecting them back to the source. This new capability enables unique applications for filter circuits beyond those suited to traditional approaches. Traditional filters are reflective in the stop band, sending signals back to the source at 100% of the power level. These reflections interact with neighboring components and often result in inter-modulation and other interferences. Reflectionless filters eliminate stop band reflections, allowing them to be paired with sensitive devices and used in applications that otherwise require circuits such as isolation amplifiers or attenuators.

Simplified Schematic and Pad description



Pad#	Description
2	RF-IN
5	RF-OUT
1,3,4,6	Ground
Die bottom	Ground

Note: 1. Bond Pad material - Gold
2. Bottom of Die - Gold plated

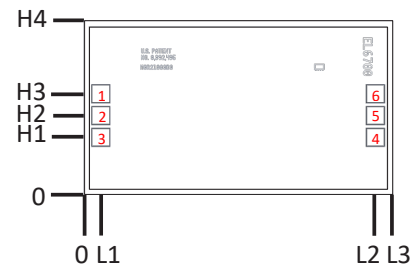


+RoHS Compliant

The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

Ordering Information: Refer to Last Page

Bonding Pad Position



Dimensions in μm, Typical

L1	L2	L3	H1	H2	H3	H4	Thickness	Bond pad size
80	1340	1420	265	365	465	800	100	78 x 78

Electrical Specifications¹ at 25°C

Parameter	F#	Frequency (MHz)	Min.	Typ.	Max.	Unit
Pass Band	Insertion Loss	DC - F1	—	1.3	—	dB
	Frequency Cut-off	F2	—	3.0	—	
	VSWR	DC - F1	—	1.3	—	:1
Stop Band	Rejection	F3 - F3'	—	28	—	dB
		F3' - F4	—	48	—	
		F4 - F5	—	50	—	
	VSWR	F3 - F3'	—	1.2	—	
		F3' - F4	—	1.4	—	:1
		F4 - F5	—	2.2	—	

¹ Measured on Mini-Circuits Characterization Test Board. Die packaged in 3x3mm, 12-lead MCLP package and soldered on TB-844-362H+.

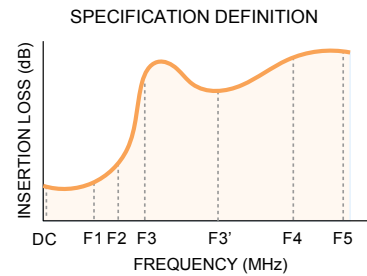
Absolute Maximum Ratings⁴

Parameter	Ratings
Operating Temperature	-55°C to +105°C
Storage Temperature	-65°C to +150°C
RF Power Input, Passband (DC-F1) ²	4W at 25°C
RF Power Input, Stopband (F2-F5) ³	1.6W at 25°C

² Passband rating derates linearly to 2W at 105°C ambient

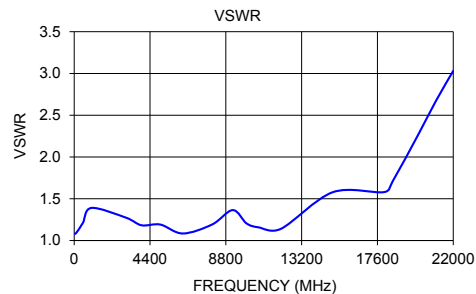
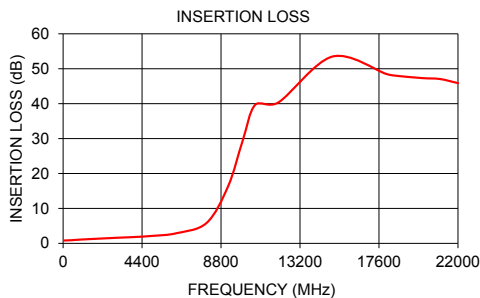
³ Stopband rating derates linearly to 0.8W at 105°C ambient

⁴ Permanent damage may occur if any of these limits are exceeded.

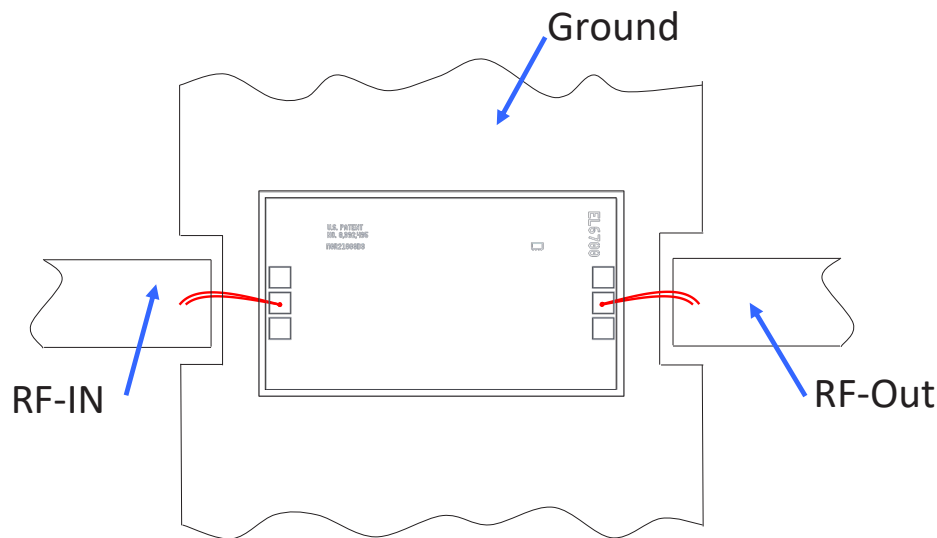


Typical Performance Data at 25°C

Frequency (MHz)	Insertion Loss (dB)	VSWR (:1)
10	0.81	1.08
100	0.83	1.09
500	0.91	1.21
1000	1.09	1.39
3000	1.60	1.27
3910	1.80	1.18
5000	2.15	1.19
6300	2.89	1.08
8000	5.87	1.19
9200	16.43	1.36
10000	29.34	1.21
10700	39.66	1.16
12000	40.37	1.14
15000	53.48	1.58
18000	48.52	1.58
18500	48.02	1.72
20000	47.32	2.28
21000	47.05	2.67
22000	45.88	3.03



Assembly Diagram



Note: Ground bond wires are optional.

Assembly and Handling Procedure

- 1. Storage**
Dice should be stored in a dry nitrogen purged desiccators or equivalent.
- 2. ESD**
MMIC Gallium Arsenide (GaAs) filter dice are susceptible to electrostatic and mechanical damage. Die are supplied in antistatic protected material, which should be opened in clean room conditions at an appropriately grounded anti-static workstation. Devices need careful handling using correctly designed collets, vacuum pickup tips or sharp antistatic tweezers to deter ESD damage to dice.
- 3. Die Attach**
The Die mounting surface must be clean and flat. Using conductive silver filled epoxy, recommended epoxies are DieMat DM6030Hk-PT/H579/H579 or Ablestik 84-1LMISR4. Apply sufficient epoxy to meet required epoxy bond line thickness, epoxy fillet height and epoxy coverage around total Die periphery. Parts shall be cured in a nitrogen filled atmosphere per manufacturer's cure condition. It is recommended to use antistatic Die pick up tools only.
- 4. Wire Bonding**
Bond pad openings in the surface passivation above the bond pads are provided to allow wire bonding to the dice gold bond pads. Thermosonic bonding is used with minimized ultrasonic content. Bond force, time, ultrasonic power and temperature are all critical parameters. Suggested wire is pure gold, 1 mil diameter. Bonds must be made from the bond pads on the Die to the package or substrate. All bond wires should be kept as short as low as reasonable to minimize performance degradation due to undesirable series inductance.

